



Vincotech

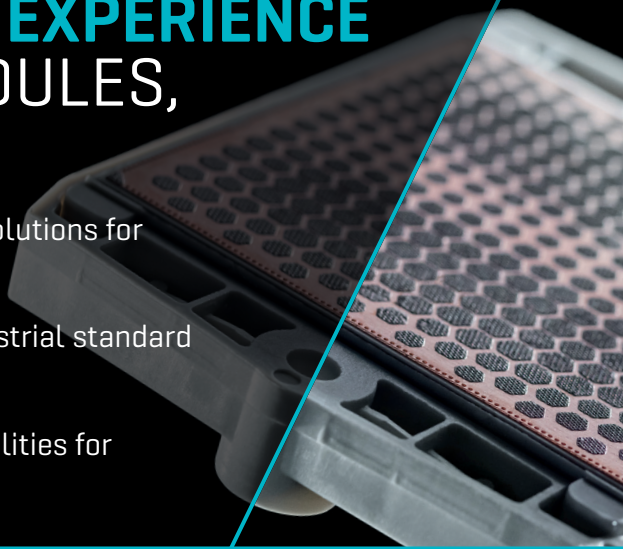
Power Module Solutions with Tandem Diodes

A compromise between
performance and cost for
industrial motor drives

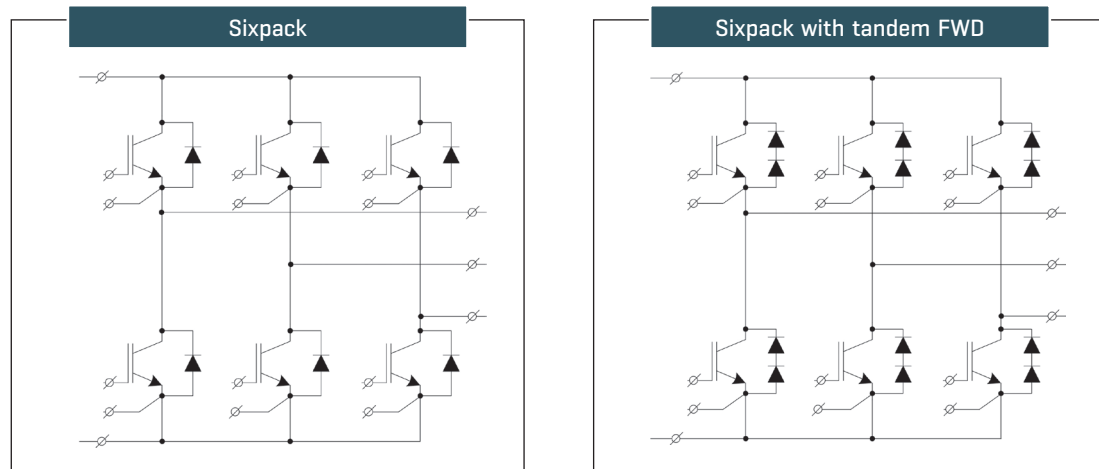
EMPOWERING YOUR IDEAS

VINCOTECH HAS 25+ YEARS OF EXPERIENCE IN POWER MODULES, PROVIDING:

- / Simple and cost-effective solutions for industry applications
- / Wide portfolio covering industrial standard topologies [Sixpack, PIM]
- / Multi-source chipset possibilities for a reliable supply chain

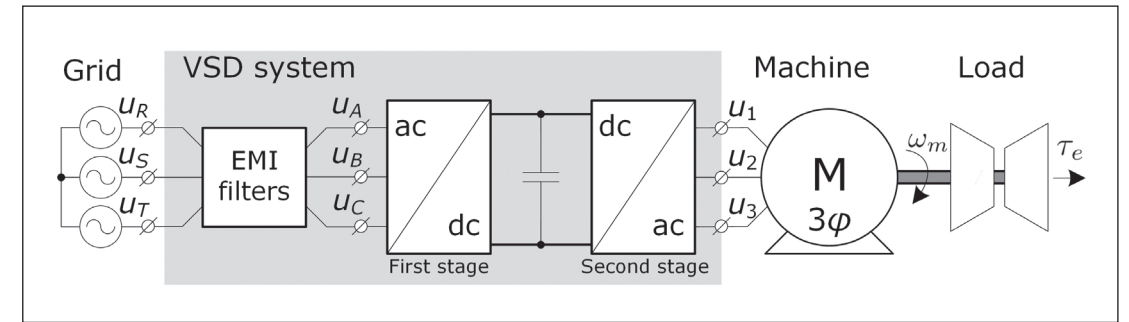


Tandem FWD are **innovative solutions for 1200 V chipset in combinations with IGBT devices** dedicated for motor drives applications



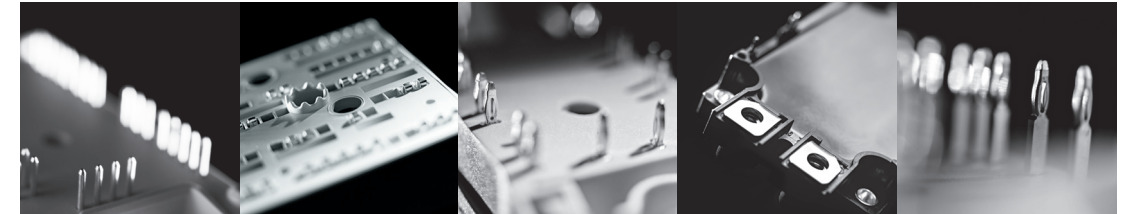
Tandem diode setup comprised of two snubber-less 650 V devices connected in series outperformed solutions using a single 1200 V FWD in terms of overall semiconductor efficiency losses at high switching frequencies [up to 16 kHz] at a far lower price point than WBG-based FWD solutions.

Standard Motor Drive Application:



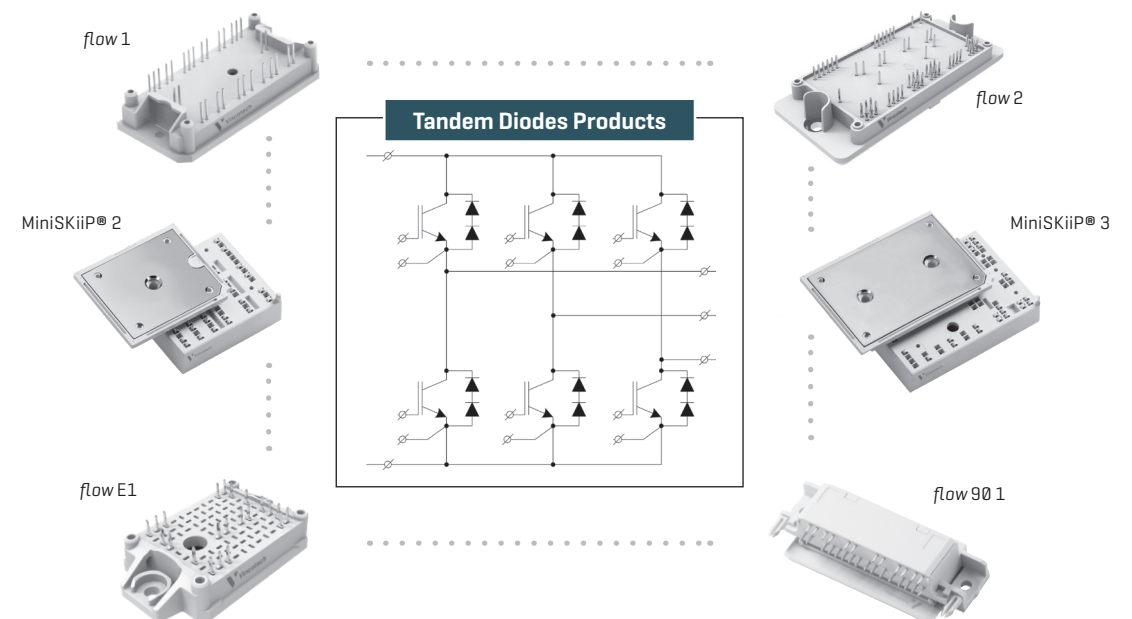
General specifications for motor drive systems:

- Switching frequency: $4 \text{ kHz} < \text{FSW} < 16 \text{ kHz}$
- DC-link voltage: $550 \text{ V} < \text{VDC} < 800 \text{ V}$
- Voltage slope limit [dv/dt]: $3 \text{ V/ns up to } 6 \text{ V/ns}$



VINCOTECH Product Roadmap

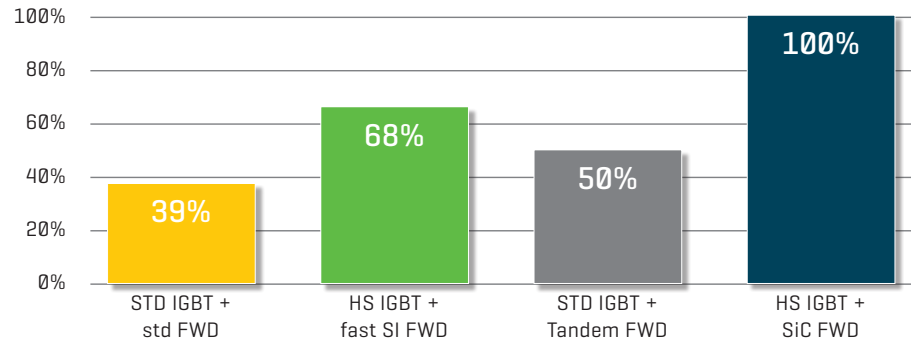
Tandem diodes solutions available for SixPack, Twin SixPack and PIM topologies including custom and industry standard power module housings.



Performance benchmark

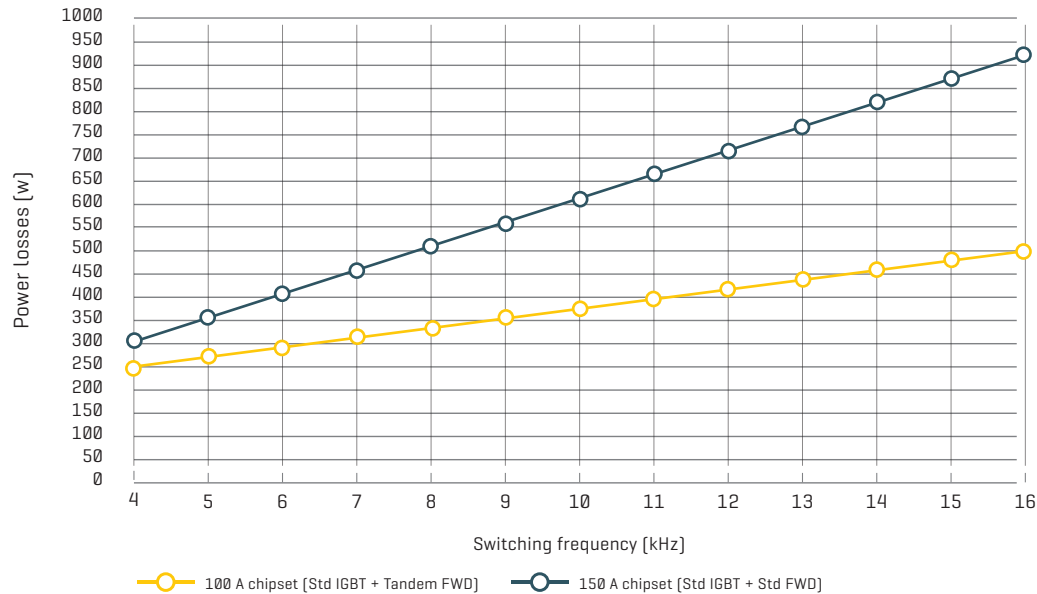
Tandem diode setup in combination with standard IGBT technology provides equilibrated trade-off between cost and performance.

Power Module Price



Semiconductor power losses

150 A [Std IGBT + Std FWD] vs 100 A [Std IGBT + Tandem FWD]

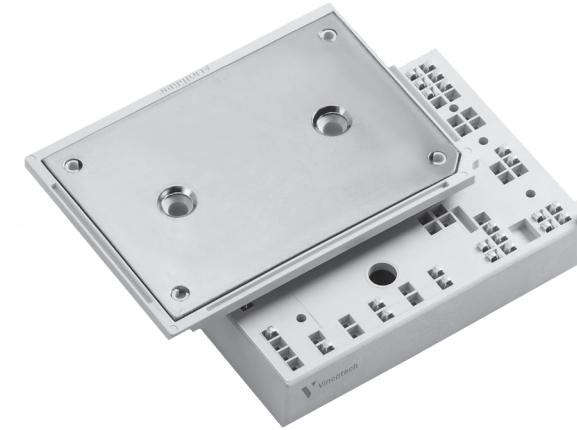


Switching frequency: 4 kHz - 16 kHz; Gate resistor selected for $dV/dt = 5 \text{ V/ns}$; DC-link voltage $U_{DC} = 800 \text{ V}$; RMS load voltage (line-to-line) $U_{OL,rms} = 400 \text{ V}$; RMS load current $I_{Orms} = 40 \text{ A}$; Load power factor $PF = 0.8$; Fundamental frequency synthesized at load $f_0 = 50 \text{ Hz}$

- / Due to low reverse recovery losses from FWD tandem setup – High efficiency is achieved
- / Taking same IGBT technology for both cases. Optimized chipset with smaller IGBT device in combination with tandem FWD that is more efficient than larger IGBT combined with standard FWD device
- / Tandem FWD solution is cost saving chipset alternative for high switching frequency

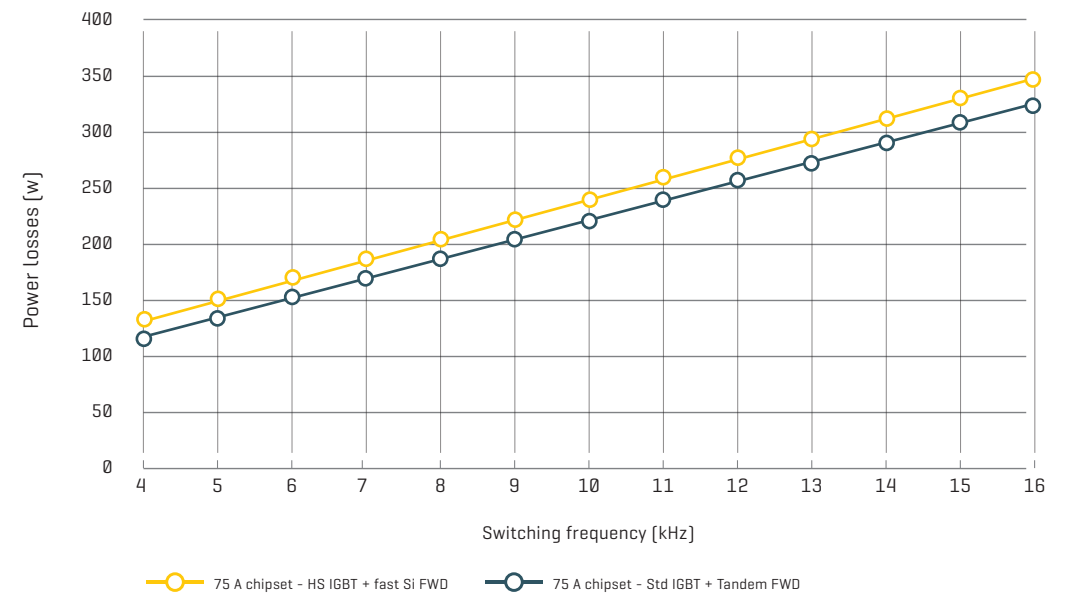
Benchmarking the Sixpack Power Module cost for different chipset realization:

- / Proposed chipset with Std IGBT with Tandem FWD is half of price of HS IGBT with SiC FWD
- / Tandem FWD solution is cost saving chipset alternative for high switching frequency comparing other chipset solutions



Semiconductor power losses

75 A [Std IGBT + Tandem FWD] vs 75 A [HS IGBT + Fast FWD]



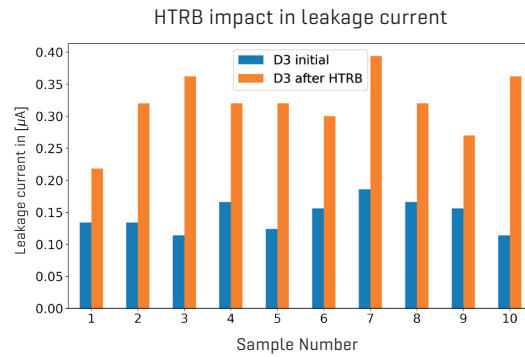
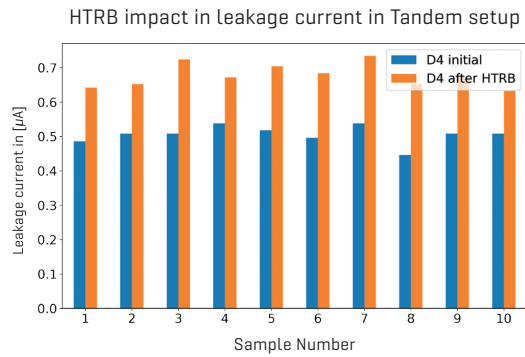
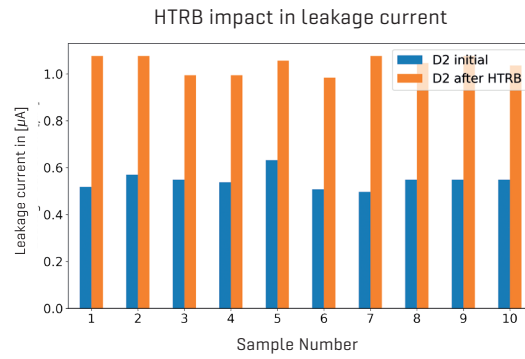
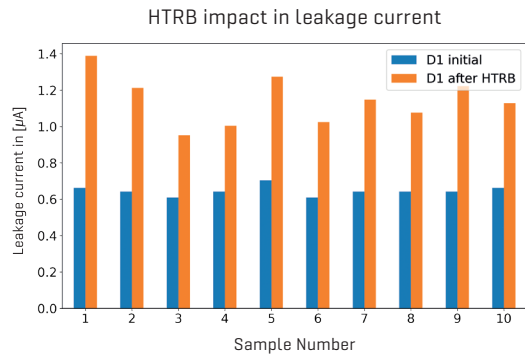
Switching frequency: 4 kHz - 16 kHz; Gate resistor selected for $dV/dt = 5 \text{ V/ns}$; DC-link voltage $U_{DC} = 800 \text{ V}$; RMS load voltage (line-to-line) $U_{OL,rms} = 400 \text{ V}$; RMS load current $I_{Orms} = 20 \text{ A}$; Load power factor $PF = 0.8$; Fundamental frequency synthesized at load $f_0 = 50 \text{ Hz}$.

- / The current is the same for IGBT and FWD devices for both cases
- / Standard IGBT in combination with Tandem FWD chipset has lower losses comparing with High Speed IGBT with fast FWD technology
- / Tandem FWD solution is cost saving chipset alternative for high switching frequency

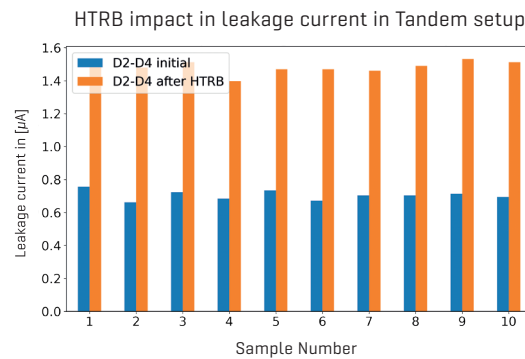
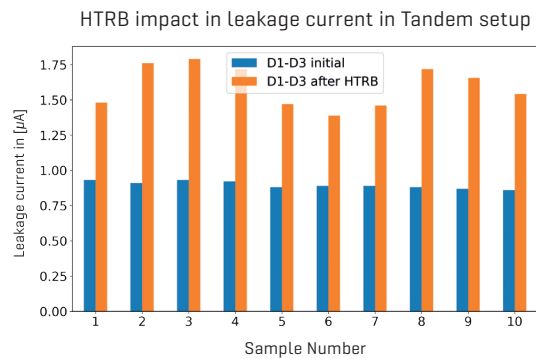
Reliability

Aging was performed for 1000 hours using the high temperature reverse bias [HTRB] test system [acc. EN60749-23] at a virtual junction temperature, T_j , of 175 °C and a reverse voltage, V_r , of 1280 V, corresponding to over 15 years in a real-world application.

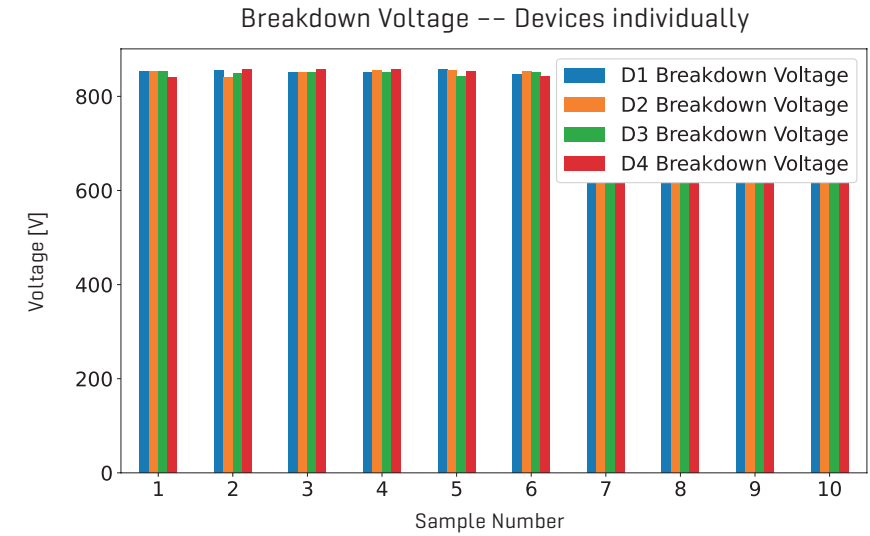
Diodes measured individually



Diodes measured in Tandem setup

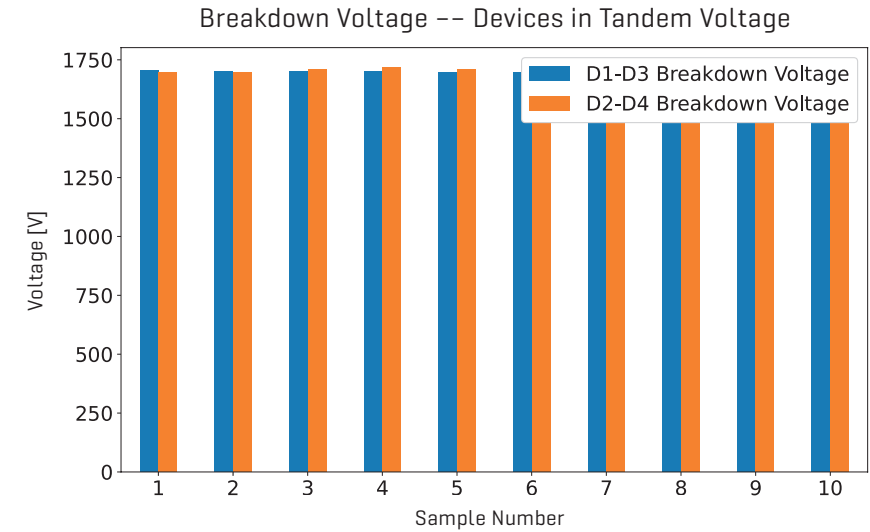


After HTRB tests, the breakdown voltage has been measured individually



Breakdown voltage measured in the range of 840 V up to 856 V

After HTRB tests, the breakdown voltage has been measured in Tandem setup



Breakdown voltage measured in the range of 1692 V up to 1716 V

Symmetrical voltage division is achieved without snubbers components



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